

UNISONIC TECHNOLOGIES CO., LTD

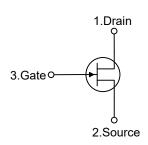
MMBFJ110 JFET

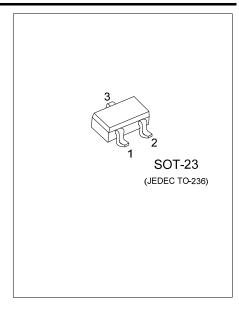
N-CHANNEL SWITCH

■ DESCRIPTION

The UTC **MMBFJ110** device is designed for digital switching applications where very low on resistance is mandatory.

■ SYMBOL

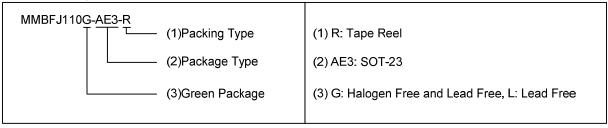




ORDERING INFORMATION

| Ordering Number | | D1 | Pin Assignment | | | Da alainan | |
|-----------------|-----------------|---------|----------------|---|---|------------|--|
| Lead Free | Halogen Free | Package | 1 | 2 | 3 | Packing | |
| MMBFJ110G-AE3-R | MMBFJ110G-AE3-R | SOT-23 | D | S | G | Tape Reel | |

Note: Pin Assignment: D: Drain S: Source G: Gate



■ MARKING



MMBFJ110 JFET

■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

| PARAMETER | SYMBOL | RATING | UNIT |
|----------------------|----------|------------|------|
| Drain-Gate Voltage | V_{DG} | 25 | V |
| Gate-Source Voltage | Vgs | -25 | V |
| Forward Gate Current | lgf | 10 | mA |
| Power Dissipation | Po | 460 | mW |
| Junction Temperature | TJ | +150 | °C |
| Storage Temperature | Тѕтс | -55 ~ +150 | °C |

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

| PARAMETER | SYMBOL | RATING | UNIT |
|---------------------|--------|--------|------|
| Junction to Ambient | θЈА | 270 | °C/W |

Note: Device mounted on FR-4 PCB 36mm × 18mm × 1.5mm, mounting pad for the collector lead minimum 6cm².

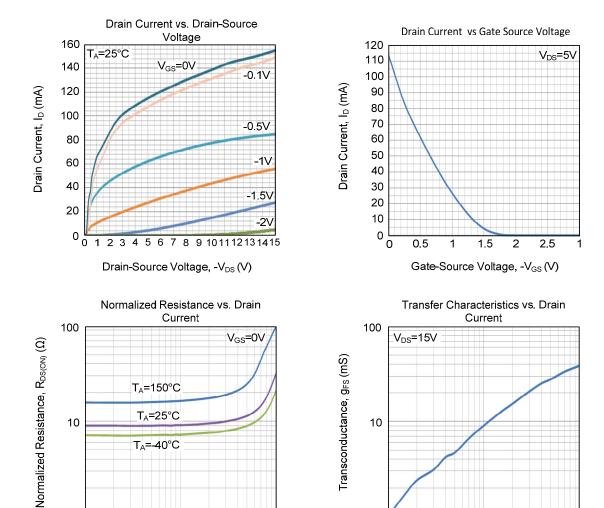
■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

| PARAMETER | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT | |
|---------------------------------|----------------------|------------------------------------------------------------------|------|-----|------|------|--|
| OFF CHARACTERISTICS | | | | | | | |
| Gate-Source Breakdown Voltage | $V_{(BR)GSS}$ | I _G =-10μA, V _{DS} =0 | -25 | | | V | |
| Gate Reverse Current | Igss | V _{GS} =-15V, V _{DS} =0 | | | -3.0 | nA | |
| | | V _{GS} =-15V, V _{DS} =0, T _A =100°C | | | -200 | nA | |
| Gate-Source Cut-Off Voltage | $V_{GS(OFF)}$ | V _{DS} =-15V, I _D =-10nA | -0.5 | | -4.0 | V | |
| ON CHARACTERISTICS | | | | | | | |
| Zero-Gate Voltage Drain Current | less | V _{DS} =-15V, V _{GS} =0 | 10 | | | mA | |
| (Note) | IDSS | | 10 | | | IIIA | |
| Drain-Source On Resistance | R _{DS(ON)} | $V_{DS} \le 0.1V$, $V_{GS}=0$ | | | 18 | Ω | |
| SMALL SIGNAL CHARACTERISTICS | | | | | | | |
| Drain-Gate & Source-Gate On | $C_{dg(on)}$ | V _{DS} =0V, V _{GS} =0, f=1MHz | | | 85 | nE | |
| Capacitance | $C_{sg(on)}$ | VDS-UV, VGS-U, I- HVIHZ | | | 60 | pF | |
| Drain-Gate & Source-Gate On | $C_{dg(off)}$ | V _{DS} =0V, V _{GS} =-10, f=1MHz | | | 15 | nE | |
| Capacitance | C _{sg(off)} | VDS-UV, VGSTU, I-TIVIMZ | | | 15 | pF | |

Note: Pulse test: pulse width \leq 300 μ s, duty cycle \leq 2%.

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TYPICAL CHARACTERISTICS



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UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. UTC reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

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Drain Current, ID (mA)

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Drain Current, I_D (mA)